

Silicon PNP Power Transistors

2SB1017

DESCRIPTION

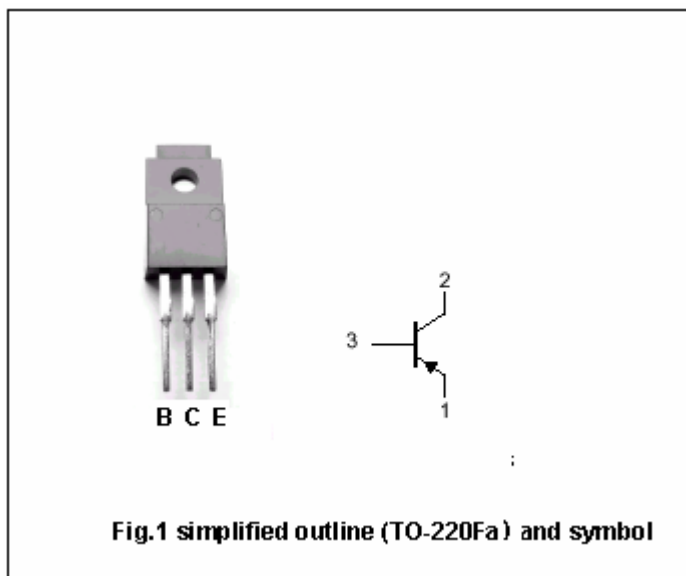
- With TO-220Fa package
- Complement to type 2SD1408

APPLICATIONS

- For power amplifications
- Recommended for 20-25W high-fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-4	A
I_B	Base current		-0.4	A
P_C	Collector power dissipation	$T_a=25$	2.0	W
		$T_C=25$	25	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA; I_B=0$	-80			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-3A; I_B=-0.3A$		-1.0	-1.7	V
V_{BE}	Base-emitter on voltage	$I_C=-3A; V_{CE}=-5V$		-1.0	-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-80V; I_E=0$			-30	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-100	μA
h_{FE-1}	DC current gain	$I_C=-0.5A; V_{CE}=-5V$	40		240	
h_{FE-2}	DC current gain	$I_C=-3A; V_{CE}=-5V$	15			
f_T	Transition frequency	$I_C=-0.5A; V_{CE}=-5V$		9		MHz
C_{OB}	Collector output capacitance	$I_E=0, f=1MHz; V_{CB}=-10V$		130		pF

◆ h_{FE-1} Classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

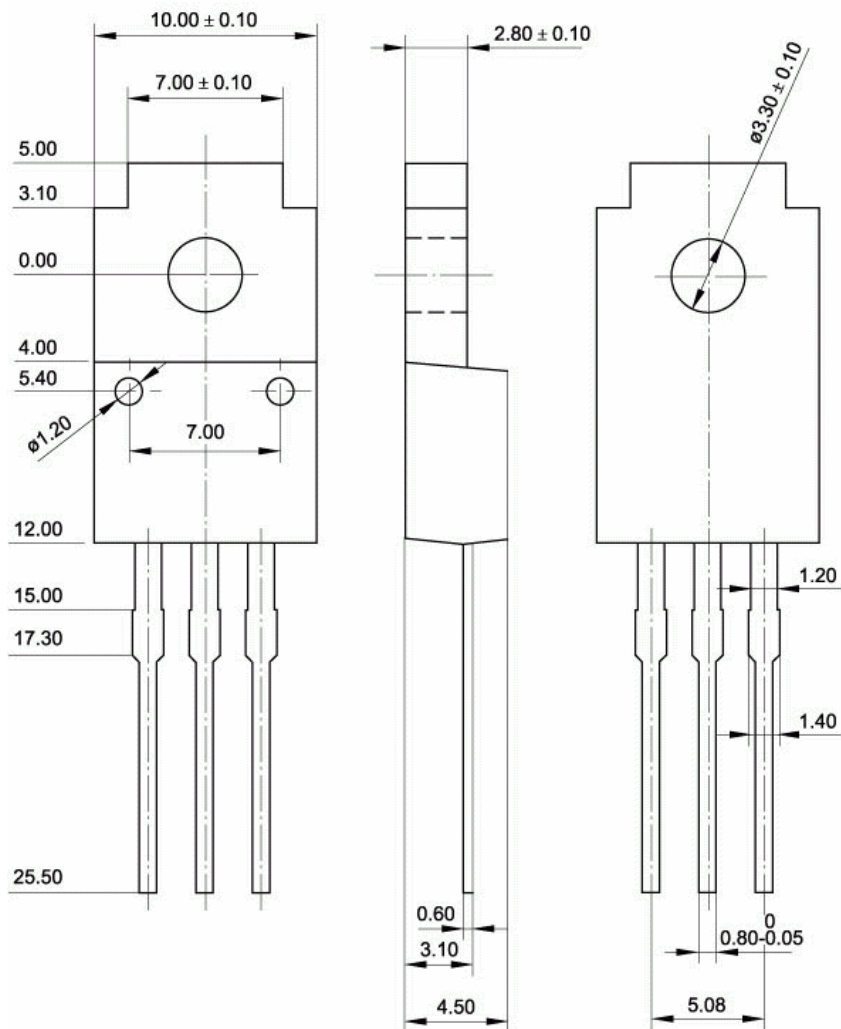


Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)

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